New Jersey Semi-Conductor Products, Inc.

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Thyristors

TIC126N

APPLICATIONS

- 12A contimunous on-state current
- 100A surge-current
- · Glass passivated
- Max I_{GT} of 20mA

SYMBOL	PARAMETER	MIN	UNIT
V _{DRM}	Repetitive peak off-state voltage	800	V
V _{RRM}	Repetitive peak reverse voltage	800	V
I _{T(AV)}	On-state current Tc=80℃	7.5	A
I _{T(RMS)}	RMS on-state current Tc=80°C	12	A
I _{TM}	Surge peak on-state current	100	Α
P _{GM}	Peak gate power $P_W \leqslant 300 \mu$ s	5	W
$\mathbf{P}_{G(AV)}$	Average gate power	1	w
Tj	Operating Junction temperature	110	°C
T _{stg}	Storage temperature	-40 ~+125	°C
R _{th(j-c)}	Thermal resistance, junction to case	2.4	°C /W
R _{th(j-a)}	Thermal resistance, junction to ambient	62.5	°C/W

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)



ELECTRICAL CHARACTERISTICS (Tc=25°C unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
I _{RRM}	Repetitive peak reverse current	V _{RM} =V _{RRM} , Tj=110℃			2.0	mA
I _{DRM}	Repetitive peak off-state current	V _{RM} =V _{RRM} , Tj=110℃			2.0	mA
V _{TM}	On-state voltage	I _{TM} = 12A			1.4	v
I _{GT}	Gate-trigger current	V _{AA} =6V; R _L =100 Ω			20	mA
V _{GT}	Gate-trigger voltage	V _{AA} =6V; R _L =100 Ω			1.5	v
I _H	Holding current	V _{AA} =6V; R _{GK} =1k Ω ,I _T =100mA			40	mA

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Quality Semi-Conductors